

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

# 2SC3267

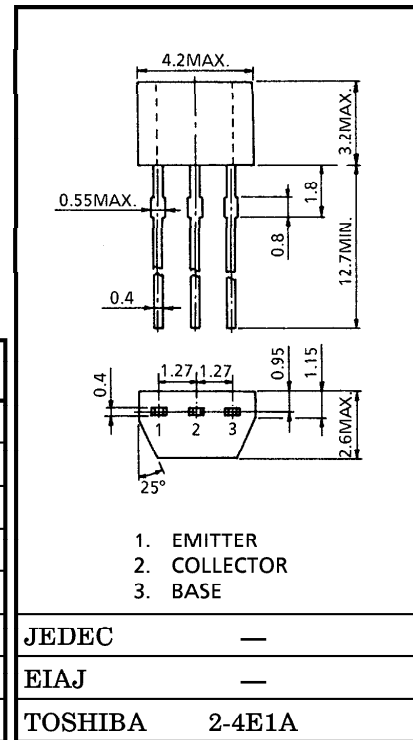
POWER AMPLIFIER APPLICATIONS  
POWER SWITCHING APPLICATIONS

Unit in mm

- Low Saturation Voltage :  $V_{CE(sat)} = 0.5V (Max.) @ I_C = 2A$
- Complementary to 2SA1297

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	20	V
Collector-Emitter Voltage	$V_{CEO}$	20	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	2	A
Base Current	$I_B$	0.5	A
Collector Power Dissipation	$P_C$	400	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$



Weight : 0.13g

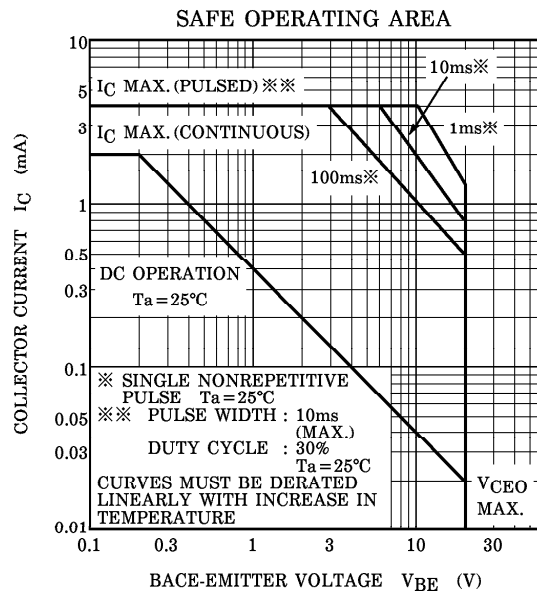
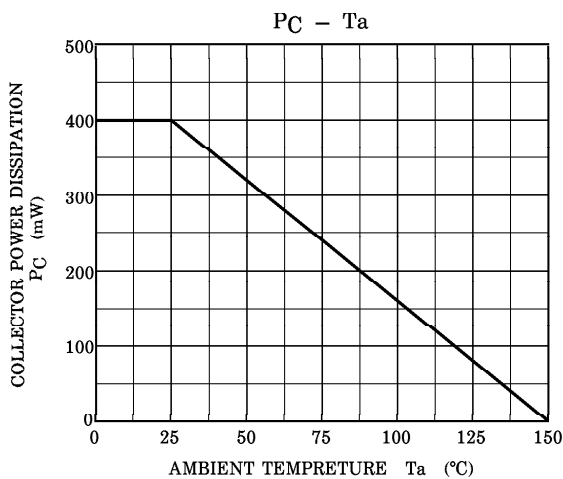
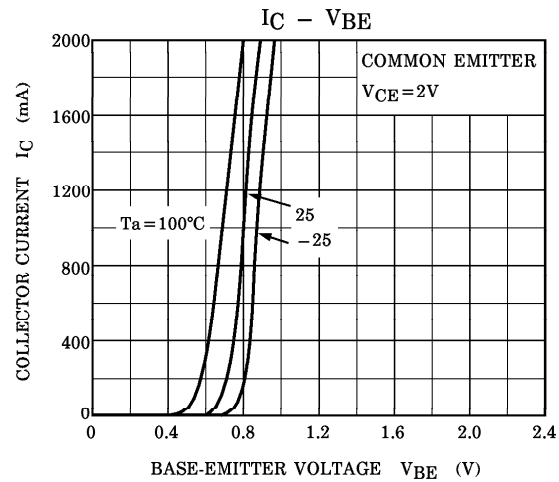
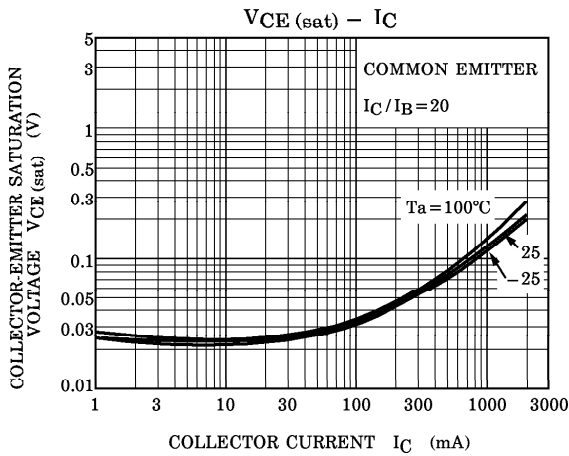
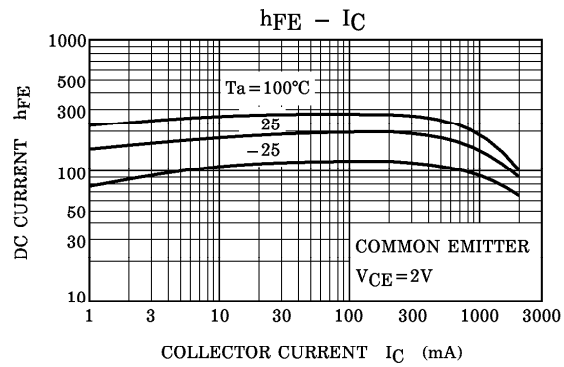
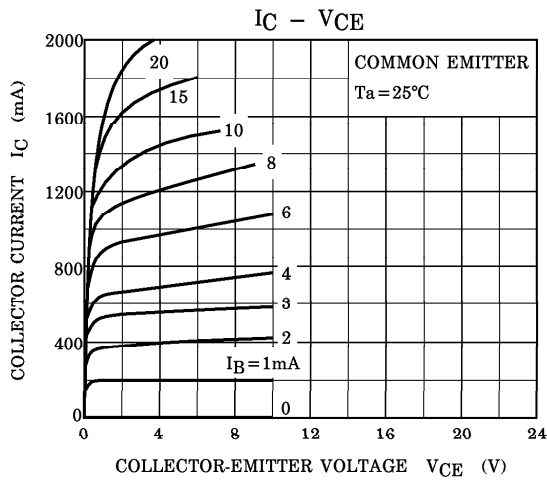
ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 20V, I_E = 0$	—	—	0.1	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 6V, I_C = 0$	—	—	0.1	$\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = 10mA, I_B = 0$	20	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR) EBO}$	$I_E = 0.1mA, I_C = 0$	6	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = 2V, I_C = 100mA$	120	—	700	
	$h_{FE(2)}$	$V_{CE} = 2V, I_C = 2A$	75	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2A, I_B = 0.1A$	—	—	0.5	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = 2V, I_C = 0.1A$	—	—	0.85	V
Transition Frequency	$f_T$	$V_{CE} = 2V, I_C = 0.5A$	—	120	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	30	—	pF

Note :  $h_{FE(1)}$  Classification Y : 120~240, GR : 200~400, BL : 350~700

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